



STS4NF100

N-channel 100V - 0.065Ω - 4A SO-8
STripFET™ II Power MOSFET

General features

Type	V _{DSS}	R _{DS(on)}	I _D
STS4NF100	100V	<0.070Ω	4A

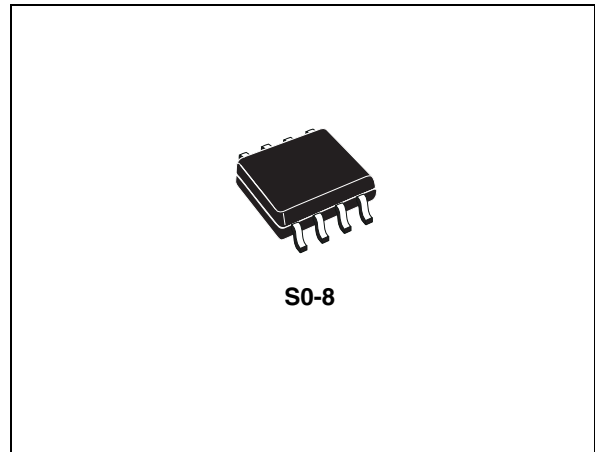
- Exceptional dv/dt capability
- 100 % avalanche tested
- Application oriented characterization

Description

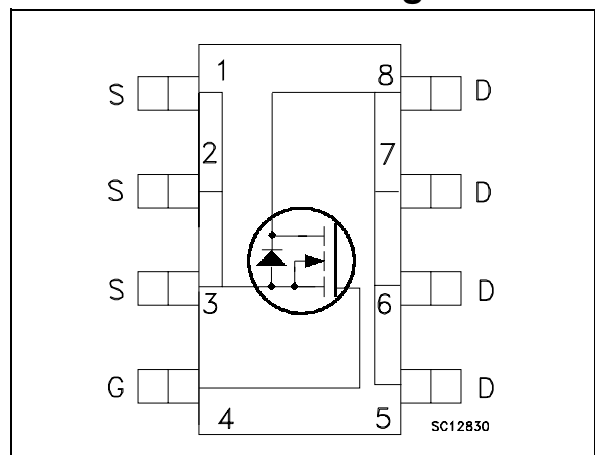
This MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency, high-frequency isolated DC-DC converters for Telecom and Computer applications. It is also intended for any applications with low gate drive requirements.

Applications

- Switching application



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STS4NF100	S4NF100	SO-8	Tape & reel

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($v_{GS} = 0$)	100	V
V_{GS}	Gate- source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	4	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	2.5	A
$I_{DM}^{(1)}$	Drain current (pulsed)	16	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	2.5	W

1. Pulse width limited by safe operating area

Table 2. Thermal data

R_{thj-a}	Thermal resistance junction-ambient Max single operation ⁽¹⁾	50	$^\circ\text{C}/\text{W}$
T_J	Thermal operating junction-ambient	-55 to 150	$^\circ\text{C}$
T_{stg}	Storage temperature	-55 to 150	$^\circ\text{C}$

1. Mounted on FR-4 board (t 10 sec.).

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	100			V
I_{DSS}	Zero gate voltage Drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating},$ $T_C = 125^{\circ}C$			1 10	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20V$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V, I_D = 2A$		0.065	0.070	W

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 2 A$		10		S
C_{iss}	Input capacitance			870		pF
C_{oss}	Output capacitance	$V_{DS} = 25V, f = 1 \text{ MHz},$ $V_{GS} = 0$		125		pF
C_{rss}	Reverse transfer capacitance			52		pF
Q_g	Total gate charge			30	41	nC
Q_{gs}	Gate-source charge	$V_{DD} = 80V, I_D = 4A,$ $V_{GS} = 10V$		6		nC
Q_{gd}	Gate-drain charge			10		nC

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 .

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	$V_{DD} = 50 V, I_D = 4A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see Figure 12)		58 45		ns ns
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 50 V, I_D = 4 A$ $R_G = 4.7\Omega, V_{GS} = 10 V$ (see Figure 12)		49 17		ns ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				4	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				16	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 4A, V_{GS} = 0$			1.2	V
t_{rr}	Reverse recovery time	$I_{SD} = 4A, V_{DD} = 30V$ $di/dt = 100A/\mu s,$ $T_j = 150^\circ C$ (see Figure 14)		100		ns
Q_{rr}	Reverse recovery charge			375		nC
I_{RRM}	Reverse recovery current			7.5		A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

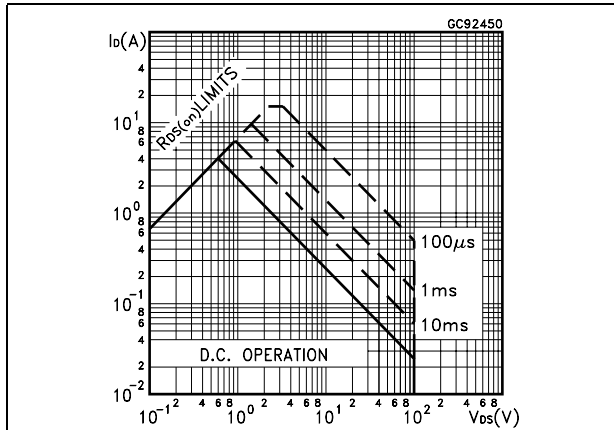


Figure 2. Thermal impedance

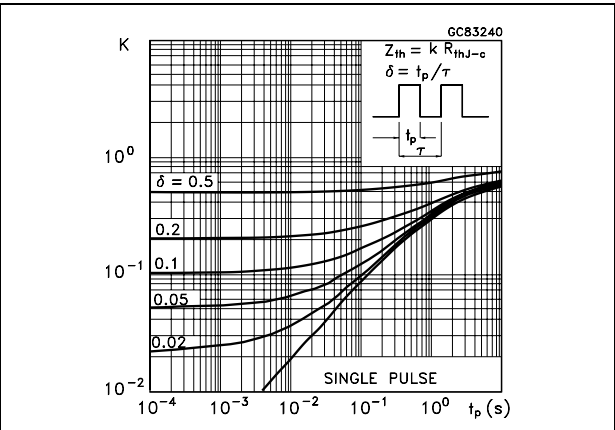


Figure 3. Output characteristics

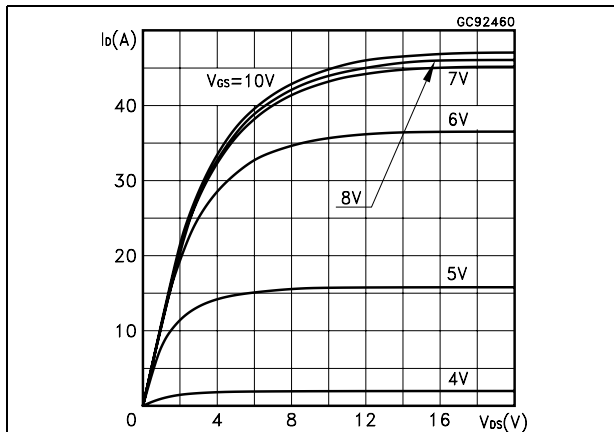


Figure 4. Transfer characteristics

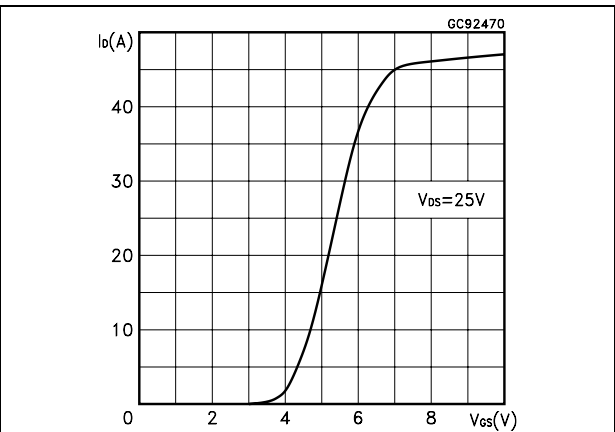


Figure 5. Transconductance

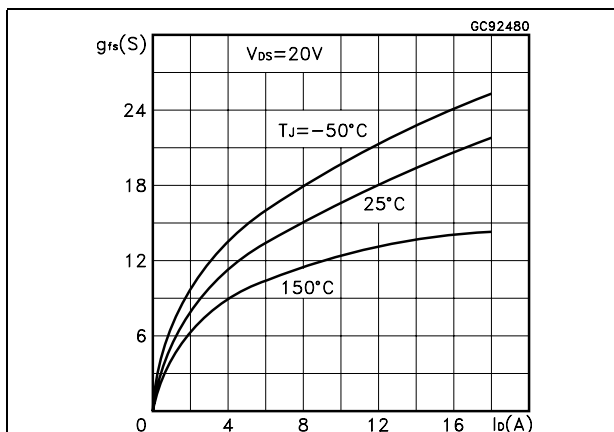


Figure 6. Static drain-source on resistance

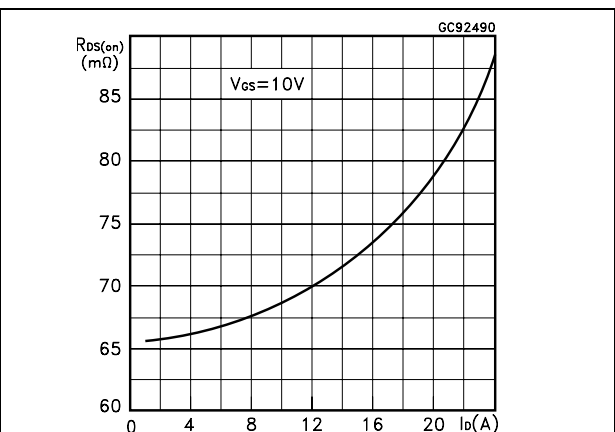


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

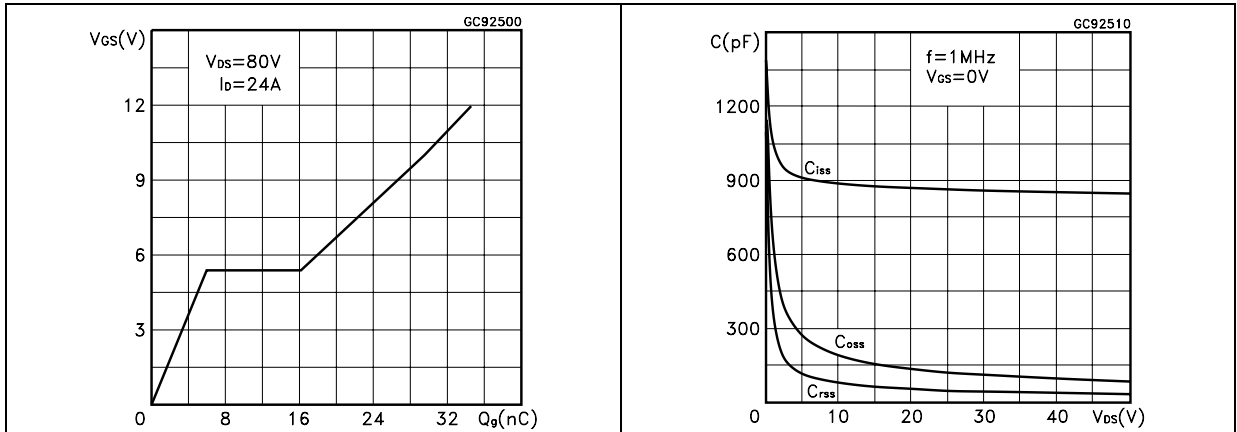


Figure 9. Normalized gate threshold voltage vs temperature Figure 10. Normalized on resistance vs temperature

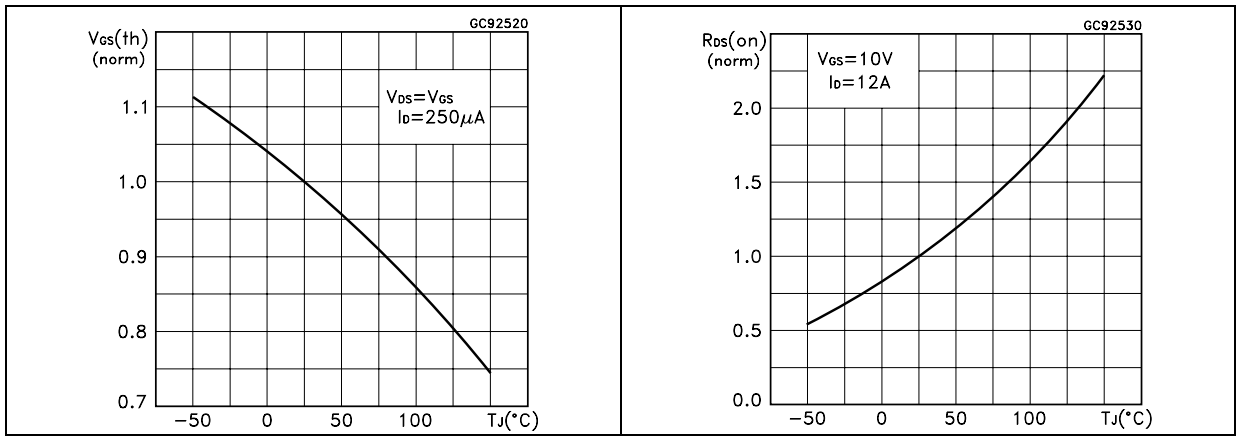
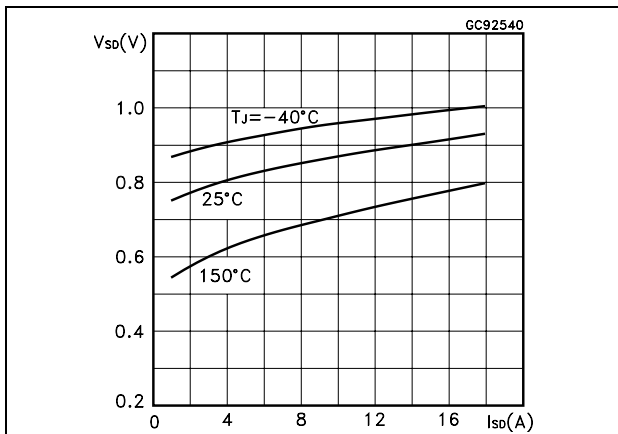


Figure 11. Source-drain diode forward characteristics



3 Test circuit

Figure 12. Switching times test circuit for resistive load



Figure 13. Gate charge test circuit

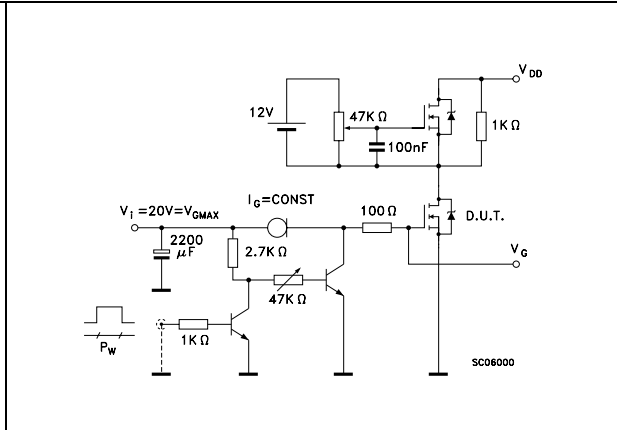


Figure 14. Test circuit for inductive load switching and diode recovery times

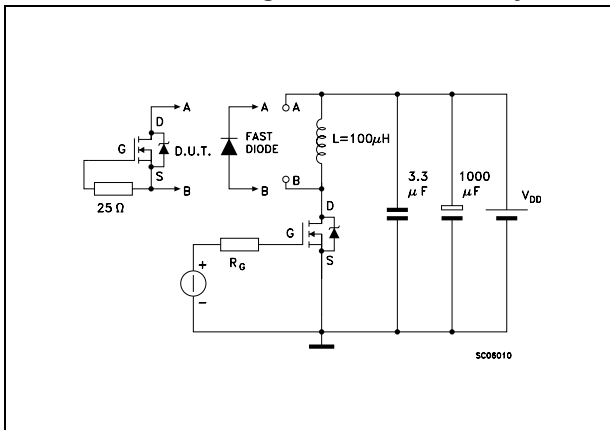


Figure 15. Unclamped Inductive load test circuit

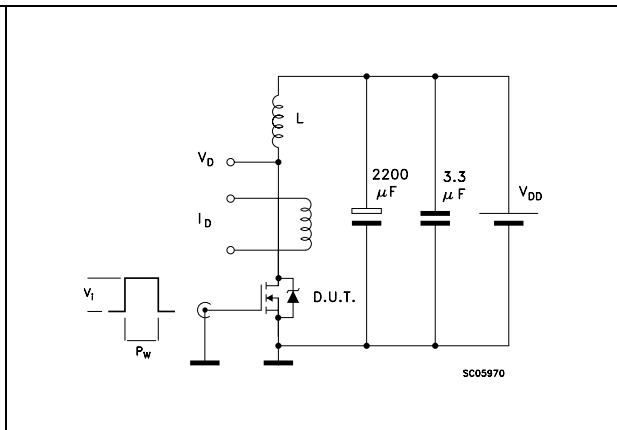


Figure 16. Unclamped inductive waveform

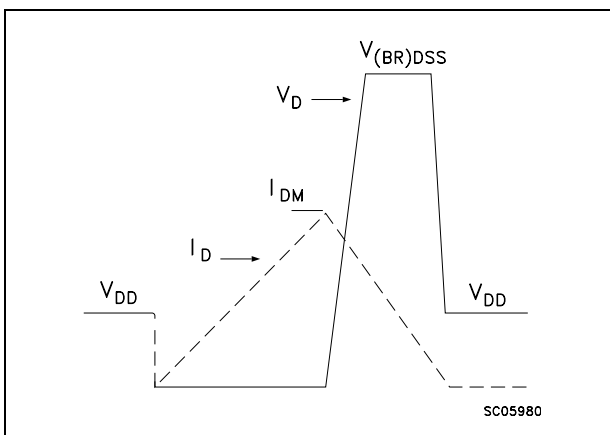
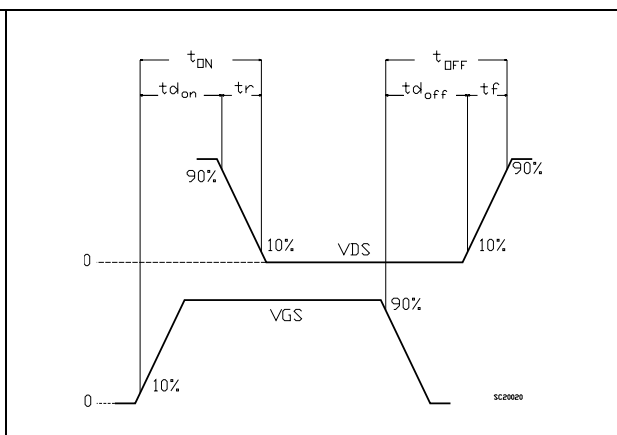


Figure 17. Switching time waveform

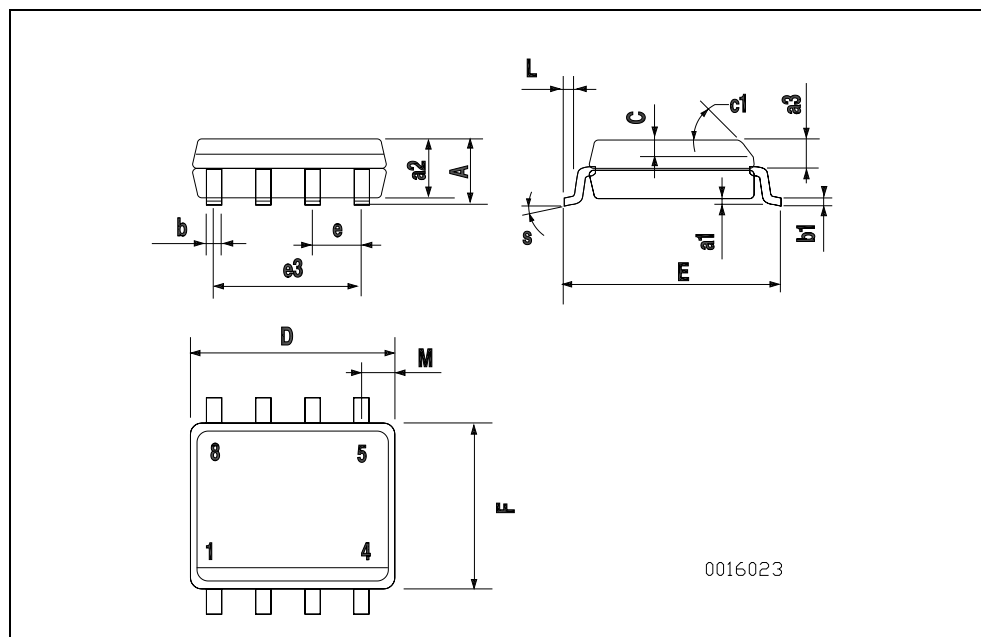


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at : www.st.com

SO-8 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



5 Revision history

Table 7. Revision history

Date	Revision	Changes
11-Sep-2006	1	First release
15-Nov-2006	2	The document has been reformatted
26-Jan-2007	3	Typo mistake on Table 2 .

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